

TOSHIBA FIELD EFFECT TRANSISTOR

SILICON N CHANNEL MOS TYPE

2SK405

TOSHIBA (DISCRETE/OPTO)

T-3A-13

AUDIO FREQUENCY POWER AMPLIFIER APPLICATION.

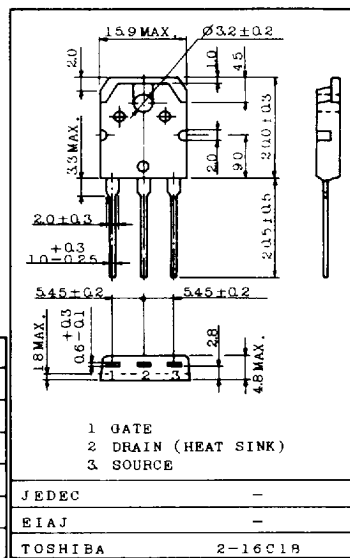
Unit in mm

FEATURES:

- High Breakdown Voltage : $V_{DS}=160V$
- High Forward Transfoer Admittance : $|Y_{fs}|=2.0S$ (Typ.)
- Complementary to 2SJ115

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	160	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	8	A
Power Dissipation ($T_c=25^\circ C$)	P_D	100	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$

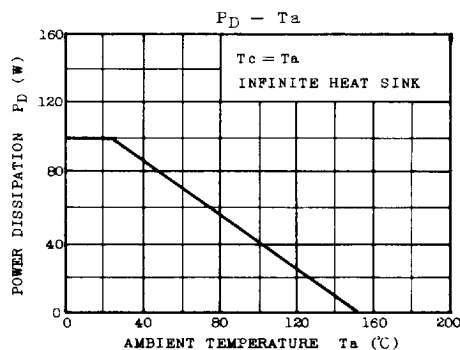
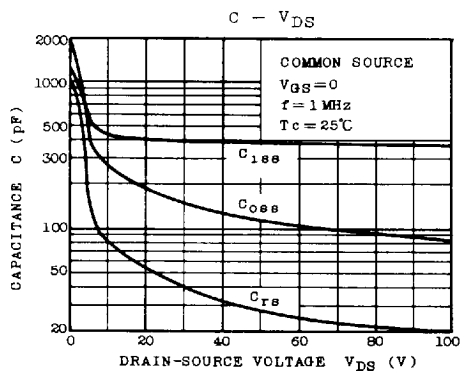
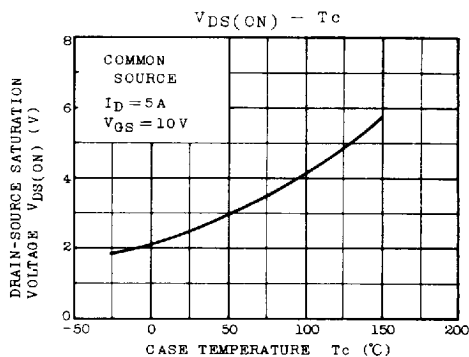
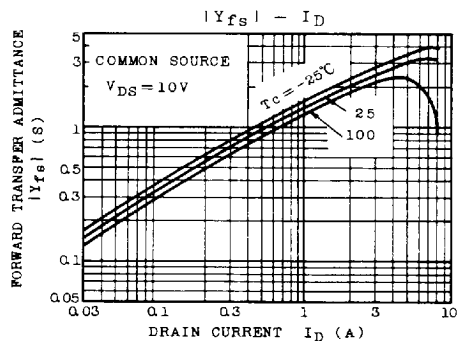
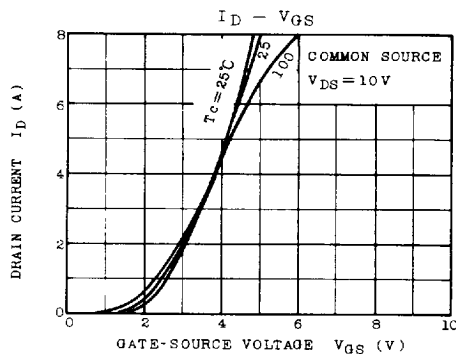
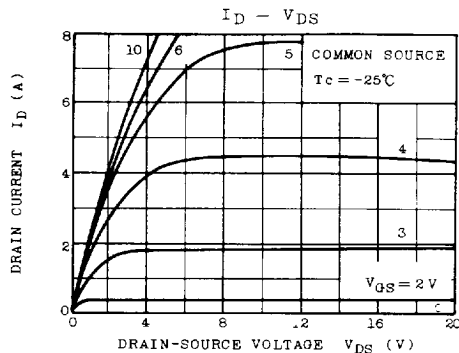


Weight : 4.6g

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{DS}=0, V_{GS}=\pm 20V$	-	-	± 1.0	μA
Drain-Source Breakdwon Voltage	$V_{(BR)DSS}$	$I_D=5mA, V_{GS}=0$	160	-	-	V
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$ (Note)	$V_{DS}=10V, I_D=0.1A$	0.8	-	2.8	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	$I_D=5A, V_{GS}=10V$	-	2.5	7.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=2A$	1.0	2.0	-	S
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0, f=1MHz$	-	430	-	pF
Output Capacitance	C_{oss}	$V_{DS}=10V, V_{GS}=0, f=1MHz$	-	260	-	pF
Reverse Transfer Capacitance	C_{rs}	$V_{DS}=10V, V_{GS}=0, f=1MHz$	-	80	-	pF

Note : $V_{GS(OFF)}$ Classification O : 0.8~1.6, Y : 1.4~2.8



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